

Silicon NPN Power Transistors

2SC1185

DESCRIPTION

- With TO-3 package
- Wide area of safe operation
- High breakdown voltage
:V_{CEO}=250V(min)

APPLICATIONS

- For voltage regulator,inverter,switching mode power supply applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

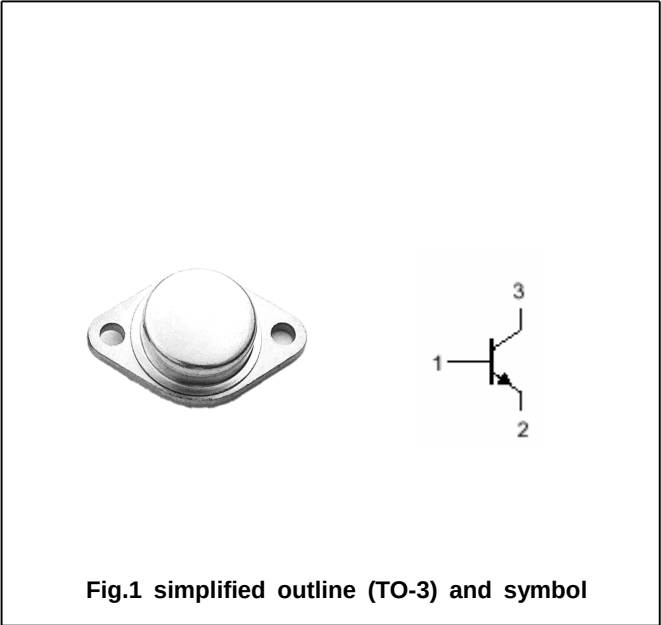


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.7	A
P _D	Total power dissipation	T _C =25?	50	W
T _J	Junction temperature		150	?
T _{stg}	Storage temperature		-55~150	?

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CHARACTERISTICS

T_j=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA; I _B =0	250			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA; I _B =100mA			1.0	V
V _{BESat}	Base-emitter saturation voltage	I _C =500mA; I _B =100mA			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.4A ; V _{CE} =10V	40		200	

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PACKAGE OUTLINE

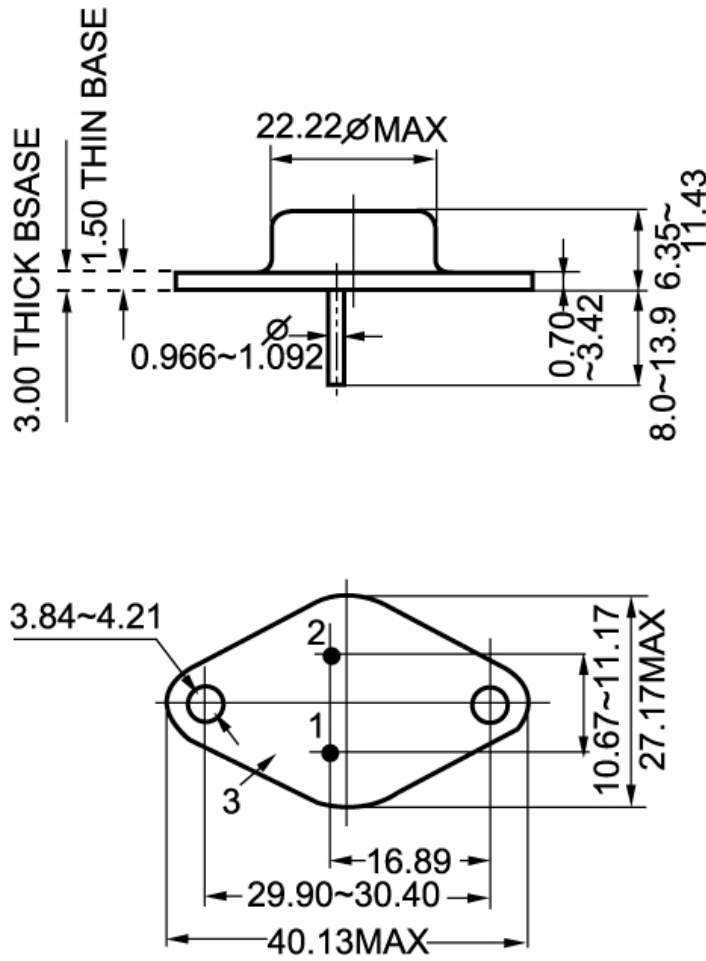


Fig.2 outline dimensions